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Author index

Abrutis, A., see Galindo, V. 208 (2000) 357
Adachi, G., see Imanaka, N. 208 (2000) 466
Aguilera Morales, S., see Falcón Rodríguez, C. 208 (2000) 651
Aitken, N.M., see Mullins, J.T. 208 (2000) 211
Aldinger, F., see Puchinger, M. 208 (2000) 153
Almuneau, G., E. Hall, S. Mathis and L.A. Coldren, Accurate control of Sb composition in AlGaAsSb alloys on InP substrates by molecular beam epitaxy 208 (2000) 113
Ambacher, O., see Kim, J.W. 208 (2000) 37
Arai, K., see Wang, H.-M. 208 (2000) 253
Aswal, D.K., T. Mori, Y. Hayakawa and M. Kumagawa, Growth of $Y_{1-z}Nd_zBa_2Cu_3O_x$ single crystals 208 (2000) 350
Ayati, M. and H.E. Lundager Madsen, Crystallization of some heavy-metal phosphates alone and in the presence of calcium ion 208 (2000) 579

Baba Ali, E., J.C. Bernède and P. Le Ray, Vanadium transition metal oxide films obtained by annealing under room atmosphere of metal layers sequentially deposited 208 (2000) 471
Bacchin, G. and T. Nishinaga, A new way to achieve both selective and lateral growth by molecular beam epitaxy: low angle incidence microchannel epitaxy 208 (2000) 1
Balkaş, C.M., Z. Sitar, L. Bergman, I.K. Shmagin, J.F. Muth, R. Kolbas, R.J. Nemanich and R.F. Davis, Growth and characterization of GaN single crystals 208 (2000) 100
Bao, C.L., see Chen, H. 208 (2000) 795
Barnett, S.A., see Pillai, M.R. 208 (2000) 79
Bennema, P., see Liu, X.-Y. 208 (2000) 687
Bergman, L., see Balkaş, C.M. 208 (2000) 100
Bergunde, T., see Dauelsberg, M. 208 (2000) 85
Bernède, J.C., see Baba Ali, E. 208 (2000) 471
Bettini, J., M.M.G. de Carvalho, M.A. Cotta, M.A.A. Pudenzi, N.C. Frateschi, A. Silva Filho, L.P. Cardoso and R. Landers, Analysis of Be doping of InGaP lattice matched to GaAs 208 (2000) 65
Betzel, C., see Eschenburg, S. 208 (2000) 657
Bill, J., see Puchinger, M. 208 (2000) 153
Boistelle, R., see Pfefer, G. 208 (2000) 615
Brinkman, A.W., see Mullins, J.T. 208 (2000) 211
Bucher, E., see Kopecek, R. 208 (2000) 289
Bulutcu, A.N., see Tanrıkulu, S.Ü. 208 (2000) 533

Cai, L.C., see Chen, H. 208 (2000) 795
Cardoso, L.P., see Bettini, J. 208 (2000) 65
Carles, J., see Mullins, J.T. 208 (2000) 211
Chang, J.-H., see Wang, H.-M. 208 (2000) 253
Chen, F., see Wang, H.L. 208 (2000) 107
Chen, H., see Zhang, S. 208 (2000) 482
Chen, H., see Li, Z.Q. 208 (2000) 786
Chen, H., L.C. Cai, C.L. Bao, J.H. Li, Q. Huang and J.M. Zhou, Two-step method to grow InAs epilayer on GaAs substrate using a new prelayer 208 (2000) 795
Chen, J.-C. and Y.-C. Lee, The influence of temperature distribution upon the structure of $LiNbO_3$ crystal rods grown using the LHPG method 208 (2000) 508
Chen, X., see Tu, C. 208 (2000) 487
Chen, Y.D., see Zhao, Q.X. 208 (2000) 117
Chen, Y.F., see Ko, H.J. 208 (2000) 389
Cheng, J.G., see Meng, X.J. 208 (2000) 541
Cheng, X.-C. and T.C. McGill, Molecular beam epitaxy growth of antimonide avalanche photodetectors with InAs/AlSb superlattice as the n-type layer 208 (2000) 183
Cheng, Z., see Zhang, S. 208 (2000) 482
Chizhov, I., A. Kahn and G. Scoles, Initial growth of 3,4,9,10-perylenetetracarboxylicdianhydride (PTCDA) on Au(1 1 1): a scanning tunneling microscopy study 208 (2000) 449
Choi, B.W. and H.N.G. Wadley, In situ studies of $Cd_{1-x}Zn_xTe$ nucleation and crystal growth 208 (2000) 219
Choi, I.-H., see Kim, J.W. 208 (2000) 37
Choi, Y., see Kim, C. 208 (2000) 804
Christides, C., see Kehagias, Th. 208 (2000) 401
Chu, J.H., see Meng, X.J. 208 (2000) 541
Chvoj, Z., see Srikanth, S. 208 (2000) 779
Coldren, L.A., see Almuneau, G. 208 (2000) 113

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Collier, A.P., C.J.D. Hetherington and M.J. Hounslow, Alignment mechanisms between particles in crystalline aggregates 208 (2000) 513
Coriell, S.R., see McFadden, G.B. 208 (2000) 726
Cotta, M.A., see Bettini, J. 208 (2000) 65
Cournil, M., see Sessiecq, P. 208 (2000) 555

Dabkowska, H., see Imanaka, N. 208 (2000) 466
Dabkowski, A., see Imanaka, N. 208 (2000) 466
Dauelsberg, M., L. Kadinski, Yu.N. Makarov, T. Bergunde, G. Strauch and M. Weyers, Modeling and experimental verification of transport and deposition behavior during MOVPE of $Ga_{1-x}In_xP$ in the Planetary Reactor 208 (2000) 85
Davis, R.F., see Balkaş, C.M. 208 (2000) 100
De Anda, F., see Olvera-Hernández, J. 208 (2000) 27
De Carvalho, M.M.G., see Bettini, J. 208 (2000) 65
De Yoreo, J.J., see Land, T.A. 208 (2000) 623
Degenhardt, M., see Eschenburg, S. 208 (2000) 657
DeLucas, L.J., see Eschenburg, S. 208 (2000) 657
Desikan, A., see Pillai, M.R. 208 (2000) 79
Duan, S., see Lu, D.-C. 208 (2000) 73
Dudley, M., see Su, C.-H. 208 (2000) 237
Durbin, S.D., see Yanagiya, S.-i. 208 (2000) 645

Edgar, J.H., see Wei, C.H. 208 (2000) 179
Eggington, P.J. and A.G. Taylor, Monitoring crystal dissolution at nanometer resolution using laser reflectometry 208 (2000) 525
Eguchi, M., see Ma, M. 208 (2000) 282
Einfeldt, S., see Selke, H. 208 (2000) 57
Eroğlu, İ., see Tanrıkulu, S.Ü. 208 (2000) 533
Eschenburg, S., M. Degenhardt, K. Moore, L.J. DeLucas, K. Peters, S. Fittkau, W. Weber and C. Betzel, Crystallization of proteinase K complexed with substrate analogue peptides on US space missions STS-91 and STS-95 208 (2000) 657

Fang, X.M., see Li, C.P. 208 (2000) 423
Falcón Rodríguez, C., S. Aguilera Morales and F. Falcón Rodríguez, Cessation of growth in crystals 208 (2000) 651
Falcón Rodríguez, F., see Falcón Rodríguez, C. 208 (2000) 651
Feltham, D.L. and M.G. Worster, Similarity solutions describing the melting of a mushy layer 208 (2000) 746
Feng, S.L., see Wang, H.L. 208 (2000) 107
Feth, S., see Su, C.-H. 208 (2000) 237
Fittkau, S., see Eschenburg, S. 208 (2000) 657
Frateschi, N.C., see Bettini, J. 208 (2000) 65
Friedman, D.J., A.G. Norman, J.F. Geisz and S.R. Kurtz, Comparison of hydrazine, dimethylhydrazine, and t-butylamine nitrogen sources for MOVPE growth of GaInNAs for solar cells 208 (2000) 11
Fujioka, H., see Ikeda, T. 208 (2000) 395
Furukawa, Y., see Niwa, K. 208 (2000) 493
Furumura, Y., see Kodama, S. 208 (2000) 165

Galindo, V., J.P. Sénateur, A. Abrutis, A. Teiserskis and F. Weiss, High quality $YBa_2Cu_3O_{7-\delta}/PrBa_2Cu_3O_{7-\delta}$ multilayers grown by pulsed injection MOCVD 208 (2000) 357
Geisz, J.F., see Friedman, D.J. 208 (2000) 11
George, A.E., see Saghir, M.Z. 208 (2000) 370
George, A.E., see Labrie, D. 208 (2000) 379
Giegé, R., see Lorber, B. 208 (2000) 665
Ginovker, A., see Saghir, M.Z. 208 (2000) 370
Ginovker, A., see Labrie, D. 208 (2000) 379
Glatz, C.E., see Waghmare, R.Y. 208 (2000) 678
Goldenstein, H., see Lima, M.S.F. 208 (2000) 709
Goldys, E.M., see Paskova, T. 208 (2000) 18
Gruy, F., see Sessiecq, P. 208 (2000) 555
Guo, S.L., see Meng, X.J. 208 (2000) 541
Guo, S.P., Y. Luo, W. Lin, O. Maksimov, M.C. Tamargo, I. Kuskovsky, C. Tian and G.F. Neumark, High crystalline quality ZnBeSe grown by molecular beam epitaxy with Be–Zn co-irradiation 208 (2000) 205
Guo, S.P., A. Shen, H. Yasuda, Y. Ohno, F. Matsukura and H. Ohno, Surfactant effect of Mn on the formation of self-organized InAs nanostructures 208 (2000) 799

Hall, E., see Almuneau, G. 208 (2000) 113
Hanada, T., see Wang, H.-M. 208 (2000) 253
Hanada, T., see Ko, H.J. 208 (2000) 389
Hara, K., see Hirose, S. 208 (2000) 49
Hark, S.K., see Zhang, X.B. 208 (2000) 231
Hatta, K., see Higuchi, M. 208 (2000) 501
Hayakawa, S., see Ikeda, T. 208 (2000) 395
Hayakawa, Y., see Aswal, D.K. 208 (2000) 350
He, J. and S. Kou, A new double crucible technique for LEC growth of In-doped GaAs crystals 208 (2000) 42
Heinke, H., see Selke, H. 208 (2000) 57
Henry, A., see Paskova, T. 208 (2000) 18
Hetherington, C.J.D., see Collier, A.P. 208 (2000) 513
Higuchi, M., K. Hatta, J. Takahashi, K. Kodaira, H. Kaneda and J. Saito, Floating-zone growth of rutile single crystals inclined at 48° to the *c*-axis 208 (2000) 501
Hiraiwa, M., see Imanaka, N. 208 (2000) 466
Hirose, S., H. Ibuka, A. Yoshida, N. Kano, K. Hara, H. Munekata and H. Kukimoto, Lattice contraction and electrical conduction of heavily carbon doped AlAs layers grown by atomic layer epitaxy 208 (2000) 49
Ho, W.-J., see Lee, C.-Y. 208 (2000) 137
Hommel, D., see Selke, H. 208 (2000) 57
Hötzel, J., see Kopecek, R. 208 (2000) 289
Hou, J.G., see Xu, W. 208 (2000) 365

Hounslow, M.J., see Collier, A.P. 208 (2000) 513
Hozawa, M., see Kobayashi, M. 208 (2000) 459
Hsu, C.-T., Growth of ZnS : Tm thin films by MOCVD 208 (2000) 259
Huang, D.D., see Liu, J.P. 208 (2000) 322
Huang, Q., see Li, Z.Q. 208 (2000) 786
Huang, Q., see Chen, H. 208 (2000) 795
Huang, Y., see Tu, C. 208 (2000) 487

Ibuka, H., see Hirose, S. 208 (2000) 49
Ikeda, T., H. Fujioka, S. Hayakawa, K. Ono, M. Oshima, M. Yoshimoto, H. Maruta, H. Koinuma, K. Inaba and R. Matsuo, Epitaxial growth of MnAs on single-crystalline Mn–Zn ferrite substrates 208 (2000) 395
Imanaka, N., M. Hiraiwa, S. Tamura, G. Adachi, H. Dabkowska and A. Dabkowski, Solid solution single crystal growth of the aluminum tungstate–scandium tungstate system by a modified CZ method 208 (2000) 466
Inaba, K., see Ikeda, T. 208 (2000) 395
Inomoto, Y., see Sakata, Y. 208 (2000) 130
Ishikawa, H., see Nakata, Y. 208 (2000) 93
Ishikawa, H., see Nishijima, Y. 208 (2000) 171
Izumi, N., see Tanaka, A. 208 (2000) 33

Janzén, E., see Syväjärvi, M. 208 (2000) 409
Jiang, A., see Tu, C. 208 (2000) 487
Jones, C.M., M.A. Larson, R.I. Ristic and J.N. Sherwood, The role of dislocations, integral strain, and supersaturation on the growth rates of sodium nitrate 208 (2000) 520
Jones, H., see Juarez-Hernandez, A. 208 (2000) 442
Juarez-Hernandez, A. and H. Jones, Growth temperatures and microstructure selection during Bridgman solidification of hypereutectic Al–La and Al–Ce alloys 208 (2000) 442

Kadinski, L., see Dauelsberg, M. 208 (2000) 85
Kahn, A., see Chizhov, I. 208 (2000) 449
Kakimoto, K., see Wang, Y. 208 (2000) 303
Kaneda, H., see Higuchi, M. 208 (2000) 501
Kano, N., see Hirose, S. 208 (2000) 49
Karakostas, Th., see Kehagias, Th. 208 (2000) 401
Karlsteen, M., see Zhao, Q.X. 208 (2000) 117
Karpov, S.Yu., see Segal, A.S. 208 (2000) 431
Kato, H., see Kodama, S. 208 (2000) 165
Katsui, A., see Matsushita, H. 208 (2000) 416
Kavanagh, K.L., see Xin, H.P. 208 (2000) 145
Kehagias, Th., Ph. Komninou, C. Christides, G. Nouet, S. Stavroyiannis and Th. Karakostas, Growth of fcc Co in sputter-deposited Co/Au multilayers with (1 1 1) texture 208 (2000) 401
Kim, C., J. Yi, S. Kim, M.H. Kim, M. Yang, Y. Choi, T.-K. Yoo and S.T. Kim, Relaxation of anisotropic domain tilting along vertical growth direction in selectively lateral overgrown GaN by hydride vapor phase epitaxy 208 (2000) 804
Kim, J.W., C.-S. Son, I.-H. Choi, Y.K. Park, Y.T. Kim, O. Ambacher and M. Stutzmann, Structural properties of $Al_xGa_{1-x}N$ grown on sapphire by molecular beam epitaxy 208 (2000) 37
Kim, K.-J., Spherulitic crystallization of 3-nitro-1,2,4-triazol-5-one in water + *N*-methyl-2-pyrrolidone 208 (2000) 569
Kim, M.H., see Kim, C. 208 (2000) 804
Kim, S., see Kim, C. 208 (2000) 804
Kim, S.T., see Kim, C. 208 (2000) 804
Kim, Y.T., see Kim, J.W. 208 (2000) 37
Kimura, M., see Tanaka, A. 208 (2000) 33
Kinoshita, K., see Kodama, S. 208 (2000) 165
Kirchner, V., see Selke, H. 208 (2000) 57
Kitamura, K., see Niwa, K. 208 (2000) 493
Ko, H.J., Y.F. Chen, Z. Zhu, T. Hanada and T. Yao, Effects of a low-temperature buffer layer on structural properties of ZnO epilayers grown on (1 1 1)CaF_2 by two-step MBE 208 (2000) 389
Kobayashi, M., T. Tsukada and M. Hozawa, Effect of internal radiative heat transfer on transition of flow modes in CZ oxide melt 208 (2000) 459
Kodaira, K., see Higuchi, M. 208 (2000) 501
Kodama, S., Y. Furumura, K. Kinoshita, H. Kato and S. Yoda, Single crystalline bulk growth of $In_{0.3}Ga_{0.7}As$ on GaAs seed using the multi-component zone melting method 208 (2000) 165
Koinuma, H., see Ikeda, T. 208 (2000) 395
Kolbas, R., see Balkaş, C.M. 208 (2000) 100
Komatsu, H., see Suzuki, Y. 208 (2000) 638
Komatsu, H., see Yanagiya, S.-i. 208 (2000) 645
Komatsu, K., see Sakata, Y. 208 (2000) 130
Komninou, Ph., see Kehagias, Th. 208 (2000) 401
Kong, M.Y., see Liu, J.P. 208 (2000) 322
Kong, M.Y., see Zhuang, Q.D. 208 (2000) 791
Kopecek, R., K. Peter, J. Hötzel and E. Bucher, Structural and electrical properties of silicon epitaxial layers grown by LPE on highly resistive monocrystalline substrates 208 (2000) 289
Kou, S., see He, J. 208 (2000) 42
Kukimoto, H., see Hirose, S. 208 (2000) 49
Kulish, N.P., see Nakhodkin, N.G. 208 (2000) 297
Kumagawa, M., see Aswal, D.K. 208 (2000) 350
Kurtz, S.R., see Friedman, D.J. 208 (2000) 11
Kurz, M. and G. Müller, Control of thermal conditions during crystal growth by inverse modeling 208 (2000) 341
Kuskovsky, I., see Guo, S.P. 208 (2000) 205
Kvam, E.P., see Pillai, M.R. 208 (2000) 79

Labrie, D., see Saghir, M.Z. 208 (2000) 370
Labrie, D., A.E. George, A.M. Simpson, B.E. Paton, A. Ginovker and M.Z. Saghir, Characterization of $CdGeAs_2$ grown by the float zone technique under microgravity 208 (2000) 379
Lan, C.W. and M.C. Liang, Three-dimensional simulation of vertical zone-melting crystal growth: symmetry breaking to multiple states 208 (2000) 327
Lan, C.W., M.C. Su and M.C. Liang, A visualization and computational study of horizontal Bridgman crystal growth 208 (2000) 717
Land, T.A. and J.J. De Yoreo, The evolution of growth modes and activity of growth sources on canavalin investigated by in situ atomic force microscopy 208 (2000) 623
Landers, R., see Bettini, J. 208 (2000) 65
Lange, F.F., see Puchinger, M. 208 (2000) 153
Larson, M.A., see Jones, C.M. 208 (2000) 520
Larson, M.A., see Waghmare, R.Y. 208 (2000) 678
Lautenschlager, P., see Lorber, B. 208 (2000) 665
Le Ray, P., see Baba Ali, E. 208 (2000) 471
Lee, C.-Y., M.-C. Wu, H.-P. Shiao and W.-J. Ho, Temperature dependence of photoluminescence from InAsP/InP strained quantum well structures grown by metalorganic chemical vapor deposition 208 (2000) 137
Lee, T.-W., see Moon, Y. 208 (2000) 160
Lee, Y.-C., see Chen, J.-C. 208 (2000) 508
Lehoczky, S.L., see Su, C.-H. 208 (2000) 237
Leonartz, K., see Suk, M.-J. 208 (2000) 809
Li, B., see Meng, X.J. 208 (2000) 541
Li, C.P., P.J. McCann and X.M. Fang, Strain relaxation in PbSnSe and PbSe/PbSnSe layers grown by liquid-phase epitaxy on (1 0 0)-oriented silicon 208 (2000) 423
Li, D.-W., see Liu, X.-Y. 208 (2000) 687
Li, J.H., see Li, Z.Q. 208 (2000) 786
Li, J.H., see Chen, H. 208 (2000) 795
Li, J.M., see Zhuang, Q.D. 208 (2000) 791
Li, J.P., see Liu, J.P. 208 (2000) 322
Li, Q.-f., see Zhu, S.-f. 208 (2000) 264
Li, W.-J., E.-W. Shi, and Z.-W. Yin, Growth habit of rutile and α-Al_2O_3 crystals 208 (2000) 546
Li, Z.Q., H. Chen, H.F. Liu, J.H. Li, L. Wan, S. Liu, Q. Huang and J.M. Zhou, MBE growth and X-ray study of high-quality cubic-GaN on GaAs(0 0 1) 208 (2000) 786
Liang, M.C., see Lan, C.W. 208 (2000) 327
Liang, M.C., see Lan, C.W. 208 (2000) 717
Lima, M.S.F. and H. Goldenstein, Morphological instability of the austenite growth front in a laser remelted iron–carbon–silicon alloy 208 (2000) 709
Lin, L.Y., see Zhuang, Q.D. 208 (2000) 791
Lin, W., see Guo, S.P. 208 (2000) 205
Lin, Y.X., see Liu, J.P. 208 (2000) 322
Liu, H.-S., see Wu, N.-C. 208 (2000) 189
Liu, H.F., see Li, Z.Q. 208 (2000) 786
Liu, J.P., D.D. Huang, J.P. Li, Y.X. Lin, D.Z. Sun and M.Y. Kong, Doping during low-temperature growth of materials for n–p–n Si/SiGe/Si heterojuction bipolar transistor by gas source molecular beam epitaxy 208 (2000) 322
Liu, S., see Li, Z.Q. 208 (2000) 786
Liu, X., see Zhang, S. 208 (2000) 482
Liu, X.-Y., M. Wang, D.-W. Li, C.S. Strom, P. Bennema and N.-B. Ming, Nucleation-limited aggregation of crystallites in fractal growth 208 (2000) 687
Liu, X.Q., see Zhao, Q.X. 208 (2000) 117
Lorber, B., J.D. Ng, P. Lautenschlager and R. Giegé, Growth kinetics and motion of thaumatin crystals during USML-2 and LMS microgravity missions and comparison with earth controls 208 (2000) 665
Lu, D.-C. and S. Duan, Quasi-thermodynamic analysis of MOVPE of AlGaN 208 (2000) 73
Lu, W., see Zhao, Q.X. 208 (2000) 117
Lundager Madsen, H.E., see Ayati, M. 208 (2000) 579
Luo, Y., see Guo, S.P. 208 (2000) 205
Luo, Z., see Tu, C. 208 (2000) 487

Ma, M., N. Nango, T. Ogawa, M. Watanabe and M. Eguchi, Study on defects in EMCZ-Si crystal by infrared light scattering tomography 208 (2000) 282
Ma, N. and J.S. Walker, A parametric study of segregation effects during vertical Bridgman crystal growth with an axial magnetic field 208 (2000) 757
Maeda, T., see Matsushita, H. 208 (2000) 416
Mah, K.W., see Yoon, S.F. 208 (2000) 197
Makarov, Yu.N., see Dauelsberg, M. 208 (2000) 85
Makarov, Yu.N., see Segal, A.S. 208 (2000) 431
Makkonen, L., Spacing in solidification of dendritic arrays 208 (2000) 772
Maksimov, O., see Guo, S.P. 208 (2000) 205
Maruta, H., see Ikeda, T. 208 (2000) 395
Mathis, S., see Almuneau, G. 208 (2000) 113
Matsukura, F., see Guo, S.P. 208 (2000) 799
Matsuo, R., see Ikeda, T. 208 (2000) 395
Matsushita, H., T. Maeda, A. Katsui and T. Takizawa, Thermal analysis and synthesis from the melts of Cu-based quaternary compounds Cu–III–IV–VI_4 and Cu_2–II–IV–VI_4 (II = Zn, Cd; III = Ga, In; IV = Ge, Sn; VI = Se) 208 (2000) 416
Matyi, R., see Su, C.-H. 208 (2000) 237
Mauri, A. and M. Moret, Growth of potassium sulfate crystals in the presence of organic dyes: in situ characterization by atomic force microscopy 208 (2000) 599
McCann, P.J., see Li, C.P. 208 (2000) 423

McFadden, G.B., S.R. Coriell and R.F. Sekerka, Analytic solution for a non-axisymmetric isothermal dendrite 208 (2000) 726
McGill, T.C., see Cheng, X.-C. 208 (2000) 183
Meng, X.J., J.G. Cheng, B. Li, S.L. Guo, H.J. Ye and J.H. Chu, Low-temperature preparation of highly (1 1 1) oriented PZT thin films by a modified sol–gel technique 208 (2000) 541
Millan, A., New method for the production of silver halide tabular crystals 208 (2000) 592
Ming, N.-B., see Liu, X.-Y. 208 (2000) 687
Mishurnyi, V.A., see Olvera-Hernández, J. 208 (2000) 27
Miyashita, S., see Suzuki, Y. 208 (2000) 638
Miyashita, S., see Yanagiya, S.-i. 208 (2000) 645
Mokhov, E.N., see Segal, A.S. 208 (2000) 431
Monemar, B., see Paskova, T. 208 (2000) 18
Moon, Y., T.-W. Lee, S. Yoon, K. Yoo and E. Yoon, Observation of two independent sources for arsenic carryover 208 (2000) 160
Moore, K., see Eschenburg, S. 208 (2000) 657
Moret, M., see Mauri, A. 208 (2000) 599
Mori, T., see Aswal, D.K. 208 (2000) 350
Motokawa, M., see Yanagiya, S.-i. 208 (2000) 645
Mukai, K., see Nakata, Y. 208 (2000) 93
Müller, G., see Kurz, M. 208 (2000) 341
Mullins, J.T., J. Carles, N.M. Aitken and A.W. Brinkman, A novel "multi-tube" vapour growth system and its application to the growth of bulk crystals of cadmium telluride 208 (2000) 211
Munekata, H., see Hirose, S. 208 (2000) 49
Muth, J.F., see Balkaş, C.M. 208 (2000) 100

Nair, M.T.S., Y. Rodríguez-Lazcano and P.K. Nair, Formation of InSb by annealing Sb_2S_3–In thin films 208 (2000) 248
Nair, P.K., see Nair, M.T.S. 208 (2000) 248
Nakada, T., see Suzuki, Y. 208 (2000) 638
Nakajima, K., see Nishijima, Y. 208 (2000) 171
Nakajima, K., see Yanagiya, S.-i. 208 (2000) 645
Nakata, Y., K. Mukai, M. Sugawara, K. Ohtsubo, H. Ishikawa and N. Yokoyama, Molecular beam epitaxial growth of InAs self-assembled quantum dots with light-emission at 1.3 μm 208 (2000) 93
Nakhodkin, N.G., N.P. Kulish, T.V. Rodionova and A.M. Strutinsky, Phase modifications in polysilicon films with fibrous and dendritic structure 208 (2000) 297
Nango, N., see Ma, M. 208 (2000) 282
Navarro-Contreras, H., see Olvera-Hernández, J. 208 (2000) 27
Nemanich, R.J., see Balkaş, C.M. 208 (2000) 100
Neumark, G.F., see Guo, S.P. 208 (2000) 205
Ng, J.D., see Lorber, B. 208 (2000) 665
Ning, D., see Wang, H.L. 208 (2000) 107
Nishijima, Y., K. Nakajima, K. Otsubo and H. Ishikawa, InGaAs single crystal with a uniform composition in the growth direction grown on an InGaAs seed using the multicomponent zone growth method 208 (2000) 171
Nishinaga, T., see Bacchin, G. 208 (2000) 1
Niwa, K., Y. Furukawa, S. Takekawa and K. Kitamura, Growth and characterization of MgO doped near stoichiometric $LiNbO_3$ crystals as a new nonlinear optical material 208 (2000) 493
Norman, A.G., see Friedman, D.J. 208 (2000) 11
Nouet, G., see Kehagias, Th. 208 (2000) 401

Ogawa, T., see Ma, M. 208 (2000) 282
Ohno, H., see Guo, S.P. 208 (2000) 799
Ohno, Y., see Guo, S.P. 208 (2000) 799
Ohsaka, K., see Rhim, W.-K. 208 (2000) 313
Ohtsubo, K., see Nakata, Y. 208 (2000) 93
Olson, K., see Saghir, M.Z. 208 (2000) 370
Olvera-Hernández, J., F. de Anda, H. Navarro-Contreras and V.A. Mishurnyi, High purity GaSb grown by LPE in a sapphire boat 208 (2000) 27
Ono, K., see Ikeda, T. 208 (2000) 395
Oshima, M., see Ikeda, T. 208 (2000) 395
Otsubo, K., see Nishijima, Y. 208 (2000) 171
Özkar, S., see Tanrıkulu, S.Ü. 208 (2000) 533

Pan, L., see Zhuang, Q.D. 208 (2000) 791
Park, Y.K., see Kim, J.W. 208 (2000) 37
Paskova, T., E.M. Goldys, R. Yakimova, E.B. Svedberg, A. Henry and B. Monemar, Influence of growth rate on the structure of thick GaN layers grown by HVPE 208 (2000) 18
Paton, B.E., see Saghir, M.Z. 208 (2000) 370
Paton, B.E., see Labrie, D. 208 (2000) 379
Peter, K., see Kopecek, R. 208 (2000) 289
Peters, K., see Eschenburg, S. 208 (2000) 657
Pfefer, G. and R. Boistelle, Theoretical morphology of adipic acid crystals 208 (2000) 615
Pillai, M.R., S.C. Theiring, S.A. Barnett, B.W. Wessels, A. Desikan and E.P. Kvam, Effect of Sb pre-deposition on the compositional profiles in MOVPE-grown InAsSb/InAs (1 1 1) multi-quantum wells 208 (2000) 79
Puchinger, M., T. Wagner, D. Rodewald, J. Bill, F. Aldinger and F.F. Lange, Gallium nitride thin layers via a liquid precursor route 208 (2000) 153
Pudenzi, M.A.A., see Bettini, J. 208 (2000) 65

Qiu, M., see Tu, C. 208 (2000) 487

Ramachandran, N. and C.-H. Su, Modeling studies of PVT growth of ZnSe: current status and future course 208 (2000) 269

Ramachandrarao, P., see Srikanth, S. 208 (2000) 779
Ramm, M.G., see Segal, A.S. 208 (2000) 431
Ramm, M.S., see Segal, A.S. 208 (2000) 431
Randolph, T.W., see Waghmare, R.Y. 208 (2000) 678
Rhim, W.-K. and K. Ohsaka, Thermophysical properties measurement of molten silicon by high-temperature electrostatic levitator: density, volume expansion, specific heat capacity, emissivity, surface tension and viscosity 208 (2000) 313
Ristic, R.I., see Jones, C.M. 208 (2000) 520
Rodewald, D., see Puchinger, M. 208 (2000) 153
Rodionova, T.V., see Nakhodkin, N.G. 208 (2000) 297
Rodríguez-Lazcano, Y., see Nair, M.T.S. 208 (2000) 248
Roenkov, A.D., see Segal, A.S. 208 (2000) 431
Ryder, P.L., see Selke, H. 208 (2000) 57

Saghir, M.Z., D. Labrie, A. Ginovker, B.E. Paton, A.E. George, K. Olson and A.M. Simpson, Float-zone crystal growth of $CdGeAs_2$ in microgravity: numerical simulation and experiment 208 (2000) 370
Saghir, M.Z., see Labrie, D. 208 (2000) 379
Saito, J., see Higuchi, M. 208 (2000) 501
Sakata, Y., Y. Inomoto and K. Komatsu, Surface migration effect and lateral vapor-phase diffusion effect for InGaAsP/InP narrow-stripe selective metal-organic vapor-phase epitaxy 208 (2000) 130
Sawada, T., see Suzuki, Y. 208 (2000) 638
Sazaki, G., see Suzuki, Y. 208 (2000) 638
Sazaki, G., see Yanagiya, S.-i. 208 (2000) 645
Scoles, G., see Chizhov, I. 208 (2000) 449
Segal, A.S., A.N. Vorob'ev, S.Yu. Karpov, E.N. Mokhov, M.G. Ramm, M.S. Ramm, A.D. Roenkov, Yu.A. Vodakov and Yu.N. Makarov, Growth of silicon carbide by sublimation sandwich method in the atmosphere of inert gas 208 (2000) 431
Sekerka, R.F., see McFadden, G.B. 208 (2000) 726
Selke, H., V. Kirchner, H. Heinke, S. Einfeldt, P.L. Ryder and D. Hommel, Polytypism in epitaxially grown gallium nitride 208 (2000) 57
Sénateur, J.P., see Galindo, V. 208 (2000) 357
Sessiecq, P., F. Gruy and M. Cournil, Study of ammonium chloride crystallization in a mixed vessel 208 (2000) 555
Shao, S.-y., see Zhu, S.-f. 208 (2000) 264
Shen, A., see Guo, S.P. 208 (2000) 799
Shen, S.C., see Zhao, Q.X. 208 (2000) 117
Sherwood, J.N., see Jones, C.M. 208 (2000) 520
Shi, E.-W., see Li, W.-J. 208 (2000) 546
Shiao, H.-P., see Lee, C.-Y. 208 (2000) 137
Shmagin, I.K., see Balkaş, C.M. 208 (2000) 100
Silva Filho, A., see Bettini, J. 208 (2000) 65
Simpson, A.M., see Saghir, M.Z. 208 (2000) 370
Simpson, A.M., see Labrie, D. 208 (2000) 379
Sitar, Z., see Balkaş, C.M. 208 (2000) 100
Södervall, U., see Zhao, Q.X. 208 (2000) 117
Son, C.-S., see Kim, J.W. 208 (2000) 37
Srikanth, S., P. Ramachandrarao and Z. Chvoj, Limits of constitutional undercooling and interfacial liquid compositions during steady-state directional solidification of binary alloys at various interface velocities 208 (2000) 779
Stavroyiannis, S., see Kehagias, Th. 208 (2000) 401
Strauch, G., see Dauelsberg, M. 208 (2000) 85
Strom, C.S., see Liu, X.-Y. 208 (2000) 687
Strutinsky, A.M., see Nakhodkin, N.G. 208 (2000) 297
Stutzmann, M., see Kim, J.W. 208 (2000) 37
Su, C.-H., M. Dudley, R. Matyi, S. Feth and S.L. Lehoczky, Characterizations of ZnSe single crystals grown by physical vapor transport 208 (2000) 237
Su, C.-H., see Ramachandran, N. 208 (2000) 269
Su, M.C., see Lan, C.W. 208 (2000) 717
Sugawara, M., see Nakata, Y. 208 (2000) 93
Suk, M.-J. and K. Leonartz, Discontinuous growth of primary naphthalene plate in camphor–naphthalene eutectic system 208 (2000) 809
Sukegawa, T., see Tanaka, A. 208 (2000) 33
Sun, D.Z., see Liu, J.P. 208 (2000) 322
Suzuki, Y., S. Miyashita, G. Sazaki, T. Nakada, T. Sawada and H. Komatsu, Effects of pressure on growth kinetics of tetragonal lysozyme crystals 208 (2000) 638
Svedberg, E.B., see Paskova, T. 208 (2000) 18
Syväjärvi, M., R. Yakimova and E. Janzén, Cross-sectional cleavages of SiC for evaluation of epitaxial layers 208 (2000) 409

Takahashi, J., see Higuchi, M. 208 (2000) 501
Takekawa, S., see Niwa, K. 208 (2000) 493
Takizawa, T., see Matsushita, H. 208 (2000) 416
Tamargo, M.C., see Guo, S.P. 208 (2000) 205
Tamura, S., see Imanaka, N. 208 (2000) 466
Tanaka, A., N. Izumi, M. Kimura and T. Sukegawa, Direct observation of LPE heterogrowth of GaAs on a GaP substrate 208 (2000) 33
Tanrıkulu, S.Ü, İ. Eroğlu, A.N. Bulutcu and S. Özkar, Crystallization kinetics of ammonium perchlorate in MSMPR crystallizer 208 (2000) 533
Taylor, A.G., see Eggington, P.J. 208 (2000) 525
Teiserskis, A., see Galindo, V. 208 (2000) 357
Theiring, S.C., see Pillai, M.R. 208 (2000) 79
Tian, C., see Guo, S.P. 208 (2000) 205
Tsai, M.-S., see Wu, N.-C. 208 (2000) 189
Tsukada, T., see Kobayashi, M. 208 (2000) 459
Tu, C., M. Qiu, Y. Huang, X. Chen, A. Jiang and Z. Luo, The study of a self-frequency-doubling laser crystal Nd^{3+}: $GdAl_3(BO_3)_4$ 208 (2000) 487

Tu, C.W., see Xin, H.P. 208 (2000) 145
Tuck, B., Diffusion of acceptors in n-type and semi-insulating InP 208 (2000) 123

Vodakov, Yu.A., see Segal, A.S. 208 (2000) 431
Vorob'ev, A.N., see Segal, A.S. 208 (2000) 431

Wadley, H.N.G., see Choi, B.W. 208 (2000) 219
Waghmare, R.Y., J.N. Webb, T.W. Randolph, M.A. Larson and C.E. Glatz, Pressure dependence of subtilisin crystallization kinetics 208 (2000) 678
Wagner, T., see Puchinger, M. 208 (2000) 153
Walker, J.S., see Ma, N. 208 (2000) 757
Wan, L., see Li, Z.Q. 208 (2000) 786
Wang, B.Q., see Zhuang, Q.D. 208 (2000) 791
Wang, H., see Wang, H.L. 208 (2000) 107
Wang, H.-M., J.-H. Chang, T. Hanada, K. Arai and T. Yao, Surface reconstruction and crystal structure of MgSe films grown on ZnTe substrates by MBE 208 (2000) 253
Wang, H.L., D. Ning, H.J. Zhu, F. Chen, H. Wang, X.D. Wang and S.L. Feng, Electronic characteristics of InAs/GaAs self-assembled quantum dots by deep level transient spectroscopy 208 (2000) 107
Wang, M., see Liu, X.-Y. 208 (2000) 687
Wang, M.-C., see Wu, N.-C. 208 (2000) 189
Wang, X.D., see Wang, H.L. 208 (2000) 107
Wang, X.X., see Zhuang, Q.D. 208 (2000) 791
Wang, Y. and K. Kakimoto, Dislocation effect on crystal–melt interface: an in situ observation of the melting of silicon 208 (2000) 303
Wang, Y.T., see Zhuang, Q.D. 208 (2000) 791
Watanabe, K., see Yanagiya, S.-i. 208 (2000) 645
Watanabe, M., see Ma, M. 208 (2000) 282
Webb, J.N., see Waghmare, R.Y. 208 (2000) 678
Weber, W., see Eschenburg, S. 208 (2000) 657
Wei, C.H. and J.H. Edgar, Unstable composition region in the wurtzite $B_{1-x-y}Ga_xAl_yN$ system 208 (2000) 179
Weiss, F., see Galindo, V. 208 (2000) 357
Wen, H.-L. and F.-S. Yen, Growth characteristics of boehmite-derived ultrafine theta and alpha-alumina particles during phase transformation 208 (2000) 696
Wessels, B.W., see Pillai, M.R. 208 (2000) 79
Weyers, M., see Dauelsberg, M. 208 (2000) 85
Willander, M., see Zhao, Q.X. 208 (2000) 117
Worster, M.G., see Feltham, D.L. 208 (2000) 746
Wu, J., see Zhuang, Q.D. 208 (2000) 791
Wu, M.-C., see Lee, C.-Y. 208 (2000) 137
Wu, N.-C., M.-S. Tsai, M.-C. Wang and H.-S. Liu, The morphology and formation mechanism of aluminum nitride nanocrystals synthesized by chemical vapor deposition 208 (2000) 189
Xin, H.P., K.L. Kavanagh and C.W. Tu, Gas-source molecular beam epitaxial growth and thermal annealing of GaInNAs/GaAs quantum wells 208 (2000) 145
Xu, W. and J.G. Hou, Growing high-quality C_{60} films by using Sb buffer layer 208 (2000) 365

Yakimova, R., see Paskova, T. 208 (2000) 18
Yakimova, R., see Syväjärvi, M. 208 (2000) 409
Yanagiya, S.-i., G. Sazaki, S.D. Durbin, S. Miyashita, K. Nakajima, H. Komatsu, K. Watanabe and M. Motokawa, Effects of a magnetic field on the growth rate of tetragonal lysozyme crystals 208 (2000) 645
Yang, H., see Zhang, S. 208 (2000) 482
Yang, M., see Kim, C. 208 (2000) 804
Yao, T., see Wang, H.-M. 208 (2000) 253
Yao, T., see Ko, H.J. 208 (2000) 389
Yasuda, H., see Guo, S.P. 208 (2000) 799
Ye, H.J., see Meng, X.J. 208 (2000) 541
Yen, F.-S., see Wen, H.-L. 208 (2000) 696
Yi, J., see Kim, C. 208 (2000) 804
Yin, Z.-W., see Li, W.-J. 208 (2000) 546
Yoda, S., see Kodama, S. 208 (2000) 165
Yokoyama, N., see Nakata, Y. 208 (2000) 93
Yoo, K., see Moon, Y. 208 (2000) 160
Yoo, T.-K., see Kim, C. 208 (2000) 804
Yoon, E., see Moon, Y. 208 (2000) 160
Yoon, S., see Moon, Y. 208 (2000) 160
Yoon, S.F., K.W. Mah, H.Q. Zheng and P.H. Zhang, Effect of V/III ratio and temperature dependence of carrier concentration in partially ordered and disordered $Ga_{0.52}In_{0.48}P$ grown on GaAs substrates 208 (2000) 197
Yoshida, A., see Hirose, S. 208 (2000) 49
Yoshimoto, M., see Ikeda, T. 208 (2000) 395
Yu, F.-l., see Zhu, S.-f. 208 (2000) 264

Zeng, Y.P., see Zhuang, Q.D. 208 (2000) 791
Zhang, P.H., see Yoon, S.F. 208 (2000) 197
Zhang, S., H. Yang, Z. Cheng, X. Liu and H. Chen, Crystal growth, thermal and optical properties of $SmCa_4O(BO_3)_3$ crystal 208 (2000) 482
Zhang, X.B. and S.K. Hark, Luminescent studies of alloy $Zn_xCd_{1-x}Se$ quantum dots grown on ZnSe by metalorganic chemical vapor-phase deposition 208 (2000) 231
Zhao, B.-j., see Zhu, S.-f. 208 (2000) 264
Zhao, Q.X., O. Zsebök, U. Södervall, M. Karlsteen, M. Willander, X.Q. Liu, Y.D. Chen, W. Lu and S.C. Shen, GaAs film deposited on $SrTiO_3$ substrate by molecular beam epitaxy 208 (2000) 117
Zheng, H.Q., see Yoon, S.F. 208 (2000) 197
Zhou, J.M., see Li, Z.Q. 208 (2000) 786
Zhou, J.M., see Chen, H. 208 (2000) 795

Zhu, H.J., see Wang, H.L. 208 (2000) 107
Zhu, S.-f., B.-j. Zhao, Q.-f. Li, F.-l. Yu, S.-y. Shao and X.-h. Zhu, Modified growth of $Cd_{1-x}Zn_xTe$ single crystals 208 (2000) 264
Zhu, X.-h., see Zhu, S.-f. 208 (2000) 264
Zhu, Z., see Ko, H.J. 208 (2000) 389
Zhuang, Q.D., J.M. Li, X.X. Wang, Y.P. Zeng, Y.T. Wang, B.Q. Wang, L. Pan, J. Wu, M.Y. Kong and L.Y. Lin, Effects of rapid thermal annealing on self-assembled InGaAs/GaAs quantum dots superlattice 208 (2000) 791
Zsebök, O., see Zhao, Q.X. 208 (2000) 117

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Journal of Crystal Growth 208 (2000) 821–823

JOURNAL OF CRYSTAL GROWTH

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Subject index

Apparatus
- for bulk crystallization of proteins 678
- for Czochralski growth 42
- for direct observation of island formation in liquid phase epitaxy 33
- for high frequency electrostatic levitation experiments 313
- for in situ nucleation study of cadmium zinc telluride bulk 219
- for liquid phase epitaxy of silicon 289
- for magnetic field assisted deposition of lysozymes 645
- for multiple chamber vapor phase epitaxy growth of cadmium telluride 211
- for visualized horizontal Bridgman growth 717

Computer simulation, Monte Carlo method
- of austenite 717
- of bond energy of adipic acid 615
- of cadmium germanium arsenide float zone microgravity 370
- of compositional profiles 79
- of convection 717
- of gallium aluminum nitride growth 73
- of gallium indium phosphide metalorganic chemical vapor deposition growth 85
- of heat transfer 459, 717
- of inverse modeling 341
- of physical vapor transport of zinc selenide growth 269
- of vertical zone melting 327

Constitutional supercooling
- of gold–copper alloy 779

Convection 327, 370, 459, 757

Dendritic growth
- of aluminum–cerium alloys 442
- of aluminum–lanthanum alloys 442
- of ammonium chloride 555
- of camphor 809
- of naphthalene 809

Device characterization
- diodes 65
- electronic materials 11, 57, 145, 289
- heterojunctions 65
- quantum structures 65, 93, 107, 137, 145, 231, 791

Diffusional control
- of acceptors in indium phosphide 123
- of dissolution 525

Diodes, see Device characterization

Dissolution, of
- ammonium chloride 555
- crystals 525
- protein crystals 645

Electronic materials, see Device characterization

Epitaxy, see Thin film growth

Etching
- chemical 379, 409

Heterojunctions, see Device characterization

Hydrodynamics, see Convection

Kinetics
- of aggregation 513
- of dissolution 525
- of growth 65, 79, 365, 442, 520, 533, 555,579, 623, 638, 645, 651, 665, 678, 709,799, 809
- of interface control 79, 160, 303
- of nucleation 33, 555, 687
- of surface poisoning 599

Lasers, crystals for
- mid-infrared 423
- neodymium doped gadolinium aluminum borate 487

Lysozyme 638

Melt growth technique
- by Bridgman–Stockbarger method
- - of cadmium zinc telluride 219
- - of silicon germanium 757
- - of sodium nitrate 717
- - theory of spacing 772
- by Czochralski method
- - of aluminum tungstate–scandium tungstate 466
- - of gallium arsenide 42
- - of samarium cobalt oxoborate 482
- - of silicon under electromagnetic field 282
- by descending ampoule with rotation
- - of cadmium zinc telluride 264
- by floating zone method

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- - of cadmium germanium arsenide 370, 379
- - of rutile 501
- by laser heated pedestal growth
- - of thin lithium niobate 508
- by laser remelting
- - of austenite 709
- by uniaxial solidification
- - of aluminum–cerium alloys 442
- - of aluminum–lanthanum alloys 442
- - of camphor 809
- - of gold–copper 779
- - of naphthalene 809
- by zone melting
- - of indium gallium phosphide 165, 171
- - theory 327
Microgravity 269, 370, 379, 657, 665
Morphological stability, of
- aluminum nitride 189
- ammonium chloride 687
- zinc selenide 269

New crystals, methods
- gallium arsenide by low angle incident microchannel epitaxy 1
- gallium arsenide on strontium titanate 117
Nucleation 687
- of ammonium chloride 555
- of neodymium barium cuprate 350
Numbers
- Peclet 269, 726
- Raleigh 327, 717

Phase diagram
- of neodymium barium cuprate 350
- of 3-nitro-1,2,4-triazol-5-one/*N*-methyl-2-pyrrolione 569
Precursor, for
- gallium indium nitride arsenide 11

Quantum structures, see Device characterization
Solid growth technique
- of C_{60} 365

Solution growth technique
- by chemical bath method
- - of indium antimonide 248
- by flux method
- - of neodymium barium cuprate 350
- - of neodymium doped gadolinium aluminum borate 487
- by high magnetic field
- - of lysozyme 645
- by hydrostatic pressure
- - of lysozyme 638
- by hydrothermal method
- - of corundum 546
- - of rutile 546
- by low temperature method
- - of alpha-alumina particles 696
- - of lead zirconate titanate 541
- - of sodium nitrate 520
- - of 3-nitro-1,2,4-triazol-5-one spherulites 569
- by sol–gel method
- - of ammonium chloride 687
- - of lead zirconate titanate 541
- by solvent mixing
- - of silver halide 592
- by top seeding method
- - of magnesium oxide doped lithium niobate 493
- theory
- - of growth 623
- - of melting mushy layers 746
Stefan problem or moving boundary problem
- of non-axisymmetric isothermal dendrite 726
- of physical vapor transport growth of zinc selenide 269
Superconductivity materials, high T_c
- bulk
- - of YNdBCO 350
- film
- - of YBCO 357
Surface structure, energy
- of canavalin 623
- of heavy metal phosphates 579
- of lysozyme crystals 638
- of potassium sulphate 599
- of silicon 289

Thin film growth technique
- by annealing
- - of metal oxides 471
- by atomic layer epitaxy
- - of aluminum arsenide 49
- by chemical solution precursor
- - of gallium nitride 153
- by chemical vapor deposition
- - of gallium nitride 18
- - of polysilicon 297
- by liquid phase epitaxy
- - of gallium antimonide 18
- - of gallium arsenide 33
- - of gallium phosphide 33
- - of lead selenide 423
- - of lead tin selenide 423
- - of silicon 289
- - of silicon carbide 409
- by magnetron sputtering
- - of copper gold 401
- by metalorganic chemical vapor deposition
- - of aluminum gallium nitride 73
- - of boron gallium aluminum nitride 179
- - of gallium arsenide 117
- - of gallium nitride 804
- - of indium arsenide 79, 160
- - of indium arsenide antimonide 79
- - of indium arsenide phosphide 137
- - of indium gallium arsenide phosphide 130

– – of indium gallium phosphide 65, 85
– – of indium nitride arsenide 11, 145
– – of PBCO 357
– – of YBCO 357
– – of zinc cadmium selenide 231
– – of zinc sulphide 259
– – theory 73
– by molecular beam epitaxy
– – of aluminum antimonide 183
– – of aluminum gallium arsenide antimonide 113
– – of aluminum gallium nitride 37
– – of gallium arsenide 1, 791
– – of gallium indium phosphide 197
– – of gallium nitride 59, 786
– – of indium arsenide 93, 107, 183, 795, 799
– – of indium gallium arsenide 791
– – of magnesium selenide 253
– – of manganese arsenide 395
– – of silicon germanium 322
– – of zinc beryllium selenide 205
– – of zinc oxide 389

Vapor growth technique
– by chemical transport
– – of aluminum nitride 189
– by evaporation and condensation
– – of aluminum nitride 100
– – of cadmium telluride 211
– – of C_{60} 365
– – of silicon carbide 409
– – of 3,4,9,10-perylenetetracarboxylic-dianhydride 449
– – of zinc selenide 237
– by physical vapor transport
– – of zinc selenide 269
– by sublimation
– – of silicon carbide 431
– by vapor diffusion
– – of proteinase 657